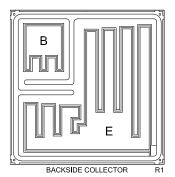


CP647-MJ11015

PNP - Darlington Transistor Die 30 Amp, 120 Volt

The CP647-MJ11015 die is a silicon PNP Darlington power transistor designed for high current applications.



MECHANICAL SPECIFICATIONS:

Die Size	211 x 211 MILS
Die Thickness	12.5 MILS
Base Bonding Pad Size	49 x 41 MILS
Emitter Bonding Pad Size	60 x 50 MILS
Top Side Metalization	AI – 50,000Å
Back Side Metalization	Ti/Ni/Ag - 1,000Å/6,000Å/10,000Å
Scribe Alley Width	4 MILS
Wafer Diameter	4 INCHES
Gross Die Per Wafer	246

MAXIMUM RATINGS: (TA=25°C)	SYMBOL		UNITS
Collector-Base Voltage	V_{CBO}	120	V
Collector-Emitter Voltage	V_{CEO}	120	V
Emitter-Base Voltage	V_{EBO}	5.0	V
Continuous Collector Current	IC	30	Α
Operating and Storage Junction Temperature	T.I. Teta	-65 to +150	°C

ELECTRICAL CHARACTERISTICS: $(T_C=25^{\circ}C \text{ unless otherwise noted})$

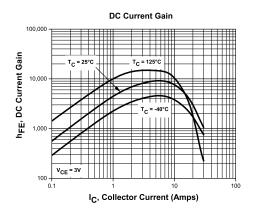
SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
ICER	V_{CE} =120V, R_{BE} =1.0k Ω		1.0	mA
ICEO	V _{CE} =50V		1.0	mA
I _{EBO}	V _{EB} =5.0V		5.0	mA
BV CEO	I _C =100mA	120		V
V _{CE} (SAT)	I _C =20A, I _B =200mA		3.0	V
V _{CE(SAT)}	I _C =30A, I _B =300mA		4.0	V
V _{BE(SAT)}	I _C =20A, I _B =200mA		3.5	V
V _{BE} (SAT)	I _C =30A, I _B =300mA		5.0	V
h _{FE}	V_{CE} =5.0V, I_{C} =20A	1.0K		
h _{FE}	V_{CE} =5.0V, I_{C} =30A	200		

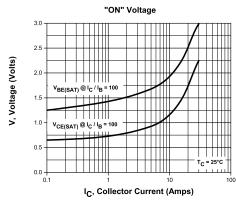
CP647-MJ11015

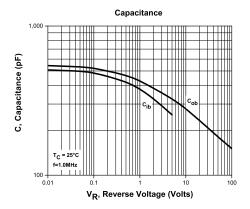
Typical Electrical Characteristics

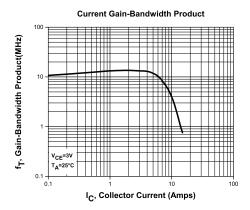


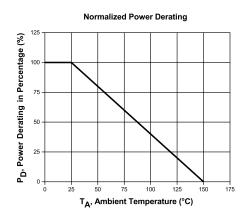
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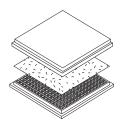






BARE DIE PACKING OPTIONS

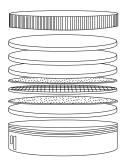




BARE DIE IN TRAY (WAFFLE) PACK

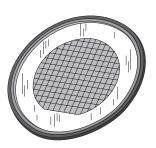
CT: Singulated die in tray (waffle) pack.
(example: CP211-PART NUMBER-CT)

CM: Singulated die in tray (waffle) pack 100% visually inspected as per MIL-STD-750, (method 2072 transistors, method 2073 diodes). (example: CP211-PART NUMBER-CM)



UNSAWN WAFER

WN: Full wafer, unsawn, 100% tested with reject die inked. (example: CP211-PART NUMBER-WN)



SAWN WAFER ON PLASTIC RING

WR: Full wafer, sawn and mounted on plastic ring, 100% tested with reject die inked.

(example: CP211-PART NUMBER-WR)

Please note: Sawn Wafer on Metal Frame (WS) is possible as a special order. Please contact your Central Sales Representative at 631-435-1110.



Visit the Central website for a complete listing of specifications: www.centralsemi.com/bdspecs

OUTSTANDING SUPPORT AND SUPERIOR SERVICES



PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- · Inventory bonding
- · Consolidated shipping options

- · Custom bar coding for shipments
- · Custom product packing

DESIGNER SUPPORT/SERVICES

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free guick ship samples (2nd day air)
- Online technical data and parametric search
- SPICE models
- · Custom electrical curves
- · Environmental regulation compliance
- · Customer specific screening
- · Up-screening capabilities

- Special wafer diffusions
- PbSn plating options
- Package details
- Application notes
- · Application and design sample kits
- Custom product and package development

REQUESTING PRODUCT PLATING

- 1. If requesting Tin/Lead plated devices, add the suffix "TIN/LEAD" to the part number when ordering (example: 2N2222A TIN/LEAD).
- 2. If requesting Lead (Pb) Free plated devices, add the suffix "PBFREE" to the part number when ordering (example: 2N2222A PBFREE).

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